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Dielectric properties of Ta₂O₅ films grown on silicon substrates plasma nitrided in N₂O

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Unfortunately, equation (1) of this paper was printed with errors. The correct form of equation (1) is:

$$J_{\text{on}} = \frac{q^2}{8\pi h \varphi} E_{\text{on}}^2 \times \exp\left(-\frac{8\pi\sqrt{2m^*}q\varphi^3}{3hE_{\text{on}}}\left(1 - \left(1 - \frac{d_{\text{on}}}{\varphi}E_{\text{on}}\right)^{3/2}\right)\right) \quad (1)$$